HEX INVERTER

- MEDIUM-SPEED OPERATION - t_{PHL}, t_{PLH} = 30 ns (TYP.) AT 10V
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100 nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD No. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

The **HCC 4069 UB** (extended temperature range) and **HCF 4069 UB** (intermediate temperature range) are monolithic integrated circuit, available in 14-lead dual in-line plastic or ceramic package, ceramic flat package and plastic micropackage.
The **HCC/HCF 4069 UB** consists of six COS/MOS inverter circuits. This device is intended for all general-purpose inverter applications where the medium-power TTL-drive and logic-level-conversion capabilities of circuits such as **HCC/HCF 4049B** Hex Inverter/Buffers are not required.

ABSOLUTE MAXIMUM RATINGS

V_{DD}*	Supply voltage: **HCC** types	-0.5 to 20	V
	HCF types	-0.5 to 18	V
V_I	Input voltage	-0.5 to V_{DD} +0.5	V
I_I	DC input current (any one input)	± 10	mA
P_{tot}	Total power dissipation (per package)	200	mW
	Dissipation per output transistor for T_{op} = full package-temperature range	100	mW
T_{op}	Operating temperature: **HCC** types	-55 to 125	°C
	HCF types	-40 to 85	°C
T_{stg}	Storage temperature	-65 to 150	°C

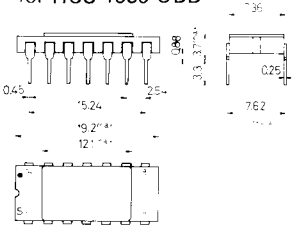
* All voltage values are referred to V_{SS} pin voltage

ORDERING NUMBERS:

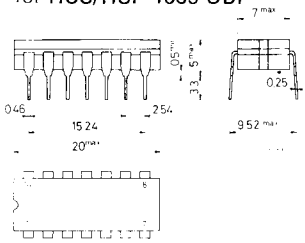
HCC 4069 UBD for dual in-line ceramic package
HCC 4069 UBF for dual in-line ceramic package, frit seal
HCC 4069 UBK for ceramic flat package
HCF 4069 UBE for dual in-line plastic package
HCF 4069 UBF for dual in-line ceramic package, frit seal
HCF 4069 UBM for plastic micropackage

MECHANICAL DATA (dimensions in mm)

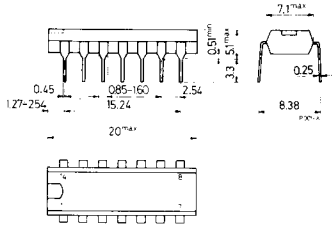
Dual in-line ceramic package for HCC 4069 UBD



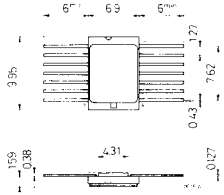
Dual in-line ceramic package for HCC/HCF 4069 UBF



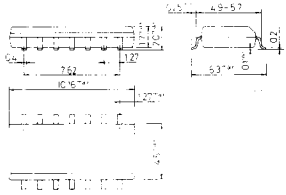
Dual in-line plastic package for HCF 4069 UBE



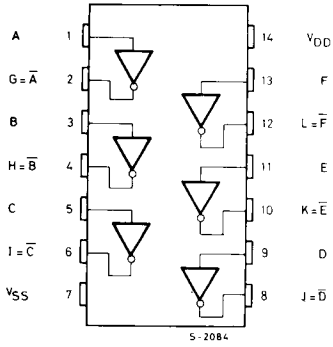
Ceramic flat package for HCC 4069 UBK



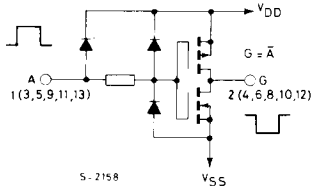
Plastic micropackage for HCF 4069 UBM



CONNECTION DIAGRAM



Schematic diagram of one of six identical inverters



RECOMMENDED OPERATING CONDITIONS

V_{DD}	Supply voltage: **HCC** types	3 to 18	V
	HCF types	3 to 15	V
V_I	Input voltage	0 to V_{DD}	V
T_{op}	Operating temperature: **HCC** types	-55 to 125	°C
	HCF types	-40 to 85	°C

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

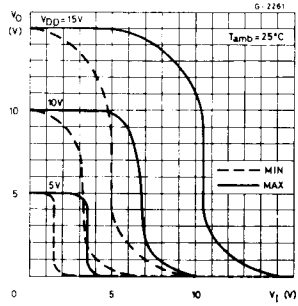
Parameter			Test conditions				Values							Unit
			V_I (V)	V_O (V)	$\|I_O\|$ (μA)	V_{DD} (V)	T_{Low}*		25°C			T_{High}*		
							Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
I_L	Quiescent current	HCC types	0/ 5			5		0.25		0.01	0.25		7.5	μA
			0/10			10		0.5		0.01	0.5		15	
			0/15			15		1		0.01	1		30	
			0/20			20		5		0.02	5		150	
		HCF types	0/ 5			5		1		0.01	1		7.5	
			0/10			10		2		0.01	2		15	
			0/15			15		4		0.01	4		30	
V_{OH}	Output high voltage		0// 5		< 1	5	4.95		4.95			4.95		V
			0/10		< 1	10	9.95		9.95			9.95		
			0/15		< 1	15	14.95		14.95			14.95		
V_{OL}	Output low voltage		5/0		< 1	5		0.05			0.05		0.05	V
			10/0		< 1	10		0.05			0.05		0.05	
			15/0		< 1	15		0.05			0.05		0.05	
V_{IH}	Input high voltage			0.5/4.5	< 1	5	4		4			4		V
				1/9	< 1	10	8		8			8		
				1.5/13.5	< 1	15	12.5		12.5			12.5		
V_{IL}	Input low voltage			4.5/0.5	< 1	5		1			1		1	V
				9/1	< 1	10		2			2		2	
				13.5/1.5	< 1	15		2.5			2.5		2.5	
I_{OH}	Output drive current	HCC types	0/ 5	2.5		5	-2		-1.6	-3.2		-1.15		mA
			0/ 5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF types	0/ 5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/ 5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
			0/15	13.5		15	-3.6		-3.0	-6.8		-2.4		
I_{OL}	Output sink current	HCC types	0/ 5	0.4		5	0.64		0.51	1		0.36		mA
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8	[1]	2.4		
		HCF types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I_{IH}, I_{IL}	Input leakage current	HCC types	0/18	Any input		18		±0.1		$\pm 10^{-5}$	±0.1		± 1	μA
		HCF types	0/15			15		±0.3		$\pm 10^{-5}$	±0.3		± 1	
C_I	Input capacitance			Any input						5	7.5			pF

* T_{Low} = − 55°C for **HCC** device: -40°C for **HCF** device.
* T_{High} = +125°C for **HCC** device: +85°C for **HCF** device.
The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD}= 5V
2V min. with V_{DD}= 10V
2.5V min. with V_{DD}= 15V

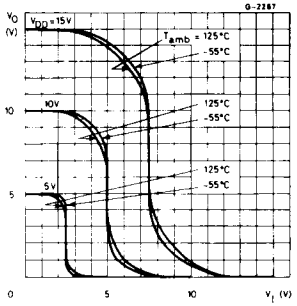
DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50 pF, R_L = 200 kΩ, typical temperature coefficient for all V_{DD} = 0.3%/°C values, all input rise and fall time = 20 ns)

Parameter	Test conditions	Values			Unit
	V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH}, t_{PHL} Propagation delay time	5		55	110	ns
	10		30	60	
	15		25	50	
t_{TLH}, t_{THL} Transition time	5		100	200	ns
	10		50	100	
	15		40	80	

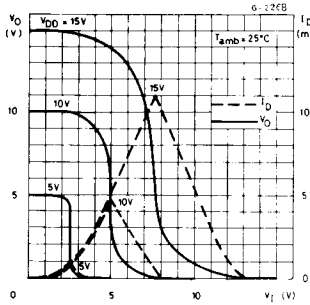
Minimum and maximum voltage transfer characteristics



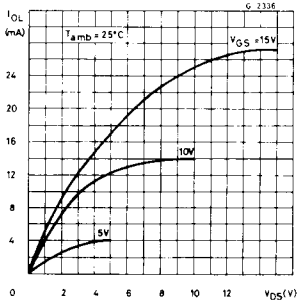
Typical voltage transfer characteristics as a function of temperature



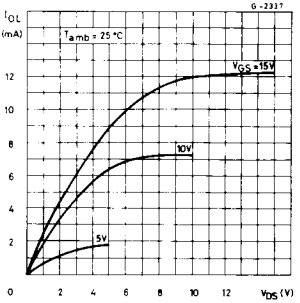
Typical current and voltage transfer characteristics



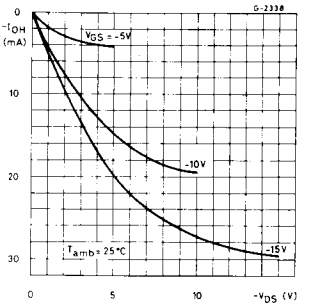
Typical output low (sink) current characteristics



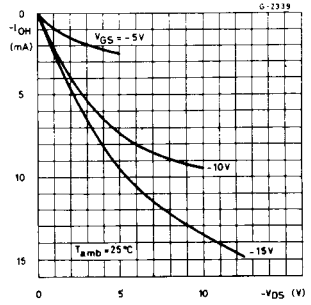
Minimum output low (sink) current characteristics



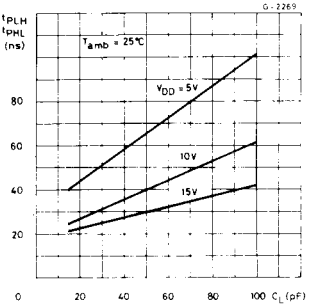
Typical output high (source) current characteristics



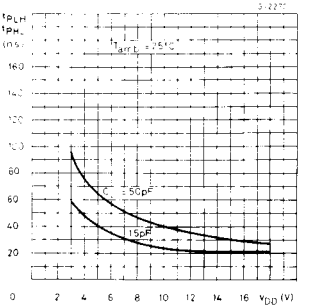
Minimum output high (source) current characteristics



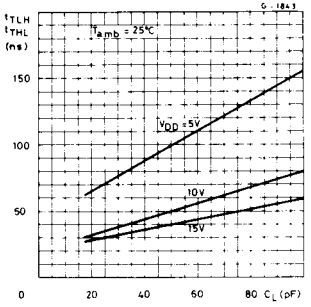
Typical propagation delay time vs. load capacitance



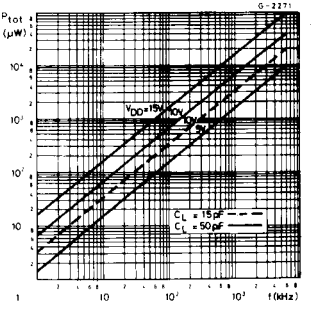
Typical propagation delay time vs. supply voltage



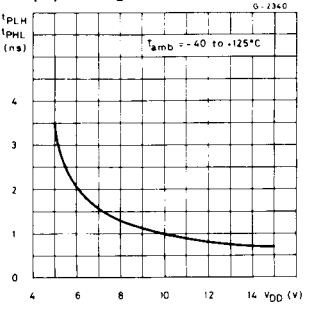
Typical transition time vs. load capacitance



Typical dynamic power dissipation/per inverter vs. frequency

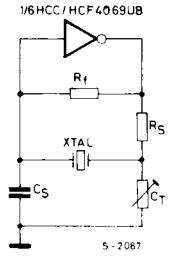


Variation of normalized propagation delay time (t_{PHL} and t_{PLH}) with supply voltage

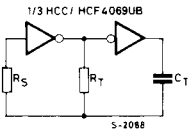


APPLICATIONS

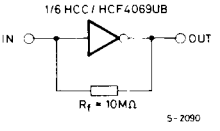
Typical crystal oscillator circuit



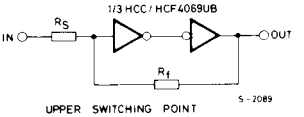
Typical RC oscillator circuit



High-input impedance amplifier



Input pulse shaping circuit (Schmitt trigger)



UPPER SWITCHING POINT

$$V_P = \frac{R_S \cdot R_f}{R_f} \cdot \frac{V_{DD}}{2}$$

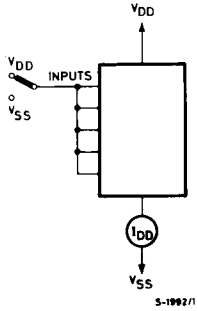
LOWER SWITCHING POINT

$$V_N = \frac{R_f - R_S}{R_f} \cdot \frac{V_{DD}}{2}$$

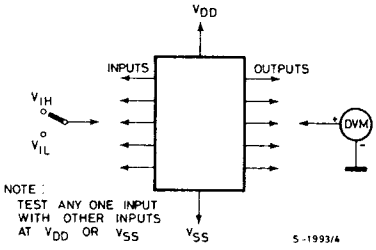
$R_f > R_S$

TEST CIRCUITS

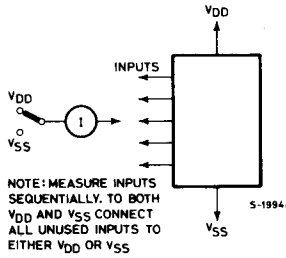
Quiescent device current



Noise immunity



Input leakage current



Dynamic electrical characteristics and waveforms